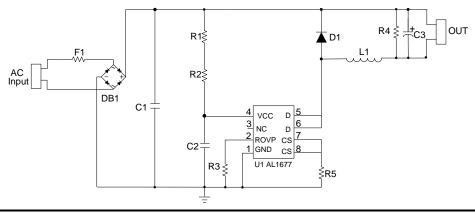


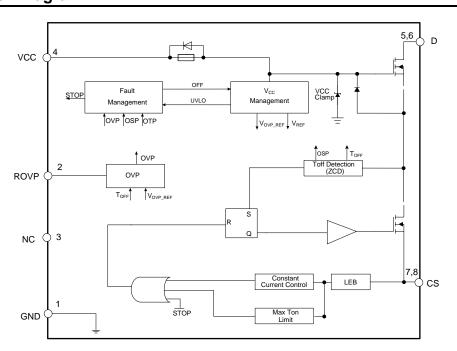
Typical Applications Circuit



Pin Descriptions

Pin Number	Pin Name	Function	
1	GND	Ground	
2	ROVP	Setting the Open Voltage of the Output	
3	NC	No Connection	
4	VCC	Ower Supply for the Device	
5,6	D	Internal High Voltage MOSFET's Drain	
7,8	CS	Current Sensing	

Functional Block Diagram





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.) (Note 4)

Symbol	Parameter		Rating	Unit
VCC	Power Supply Voltage		18	V
		AL1677-05BS-13	500	V
.,		AL1677-08BS-13	500	V
V_D	Voltage on D Pin	AL1677-10BS-13	500	V
		AL1677-20BS-13	500	V
		AL1677-05BS-13	0.5	А
	Continuous Drain Current T _c = +25°C	AL1677-08BS-13	0.8	Α
I _D		AL1677-10BS-13	1.0	Α
		AL1677-20BS-13	2.0	Α
V _{CS}	Voltage on CS Pin		-0.3 to 7	V
V _{ROVP}	Voltage on ROVP Pin		-0.3 to 7	V
TJ	Operating Junction Temperature		-40 to +150	°C
T _{STG}	Storage Temperature		-65 to +150	°C
T _{LEAD}	Lead Temperature (Soldering, 10 seconds)		+260	°C
P_{D}	Power Dissipation and Thermal Characteristics (T _A = +50°C)		0.65	W
$\theta_{\sf JA}$	Thermal Resistance (Junction to Ambient)		190	°C/W
	ESD (Human Body Model)		2,000	V
-	ESD (Machine Model)		200	V

Note:

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
T _A (Note 5)	Ambient Temperature	-40	+105	°C

Note: 5. The device can operate normally at +125°C ambient temperature under the condition that the junction temperature is less than +150°C.

^{4.} Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
UVLO Section						
V _{TH (ST)}	Startup Threshold	_	_	14.5	_	V
V _{OPR} (Min)	Minimal Operating Voltage	After Turn On	_	8.5	_	V
Vcc_clamp	Vcc Clamp Voltage	_	-	16.2	-	V
Standby Current Section						
Ist	Start-Up Current	V _{CC} = V _{TH (ST)} -0.5V, Before Start Up	_	170	_	μΑ
I _{CC (OPR)}	Operating Current	Static	-	100	-	μΑ
Internal High Voltage MOS	SFET					
		AL1677-05BS-13	_	24	26	
D	Drain Course On State Presistance	AL1677-08BS-13	_	16	20	
$R_{DS(on)}$	Drain-Source On-State Resistance	AL1677-10BS-13	-	10	12	Ω
		AL1677-20BS-13	-	5.4	6	
	Continuous Drain-Source Current	AL1677-05BS-13	-	_	0.5	A
		AL1677-08BS-13	_	_	0.8	
I _{DS}		AL1677-10BS-13	_	_	1.0	
		AL1677-20BS-13	_	_	2.0	
	Drain-Source Voltage	AL1677-05BS-13	500	_	-	V
		AL1677-08BS-13	500	_	-	
V_{DS}		AL1677-10BS-13	500	_	_	
		AL1677-20BS-13	500	_	_	
		AL1677-05BS-13	-	-	1	μΑ
	Davis Course Lords as Course	AL1677-08BS-13	_	_	1	
I _{DSS}	Drain-Source Leakage Current	AL1677-10BS-13	-	-	1	
		AL1677-20BS-13	_	_	1	
ROVP Section						
V _{ROVP}	Reference Voltage of ROVP pin	_	_	0.5	_	V
Current Sense Section						
V _{CS-REF}	Current Sense Reference	_	0.388	0.400	0.412	V
t _{ON_MIN}	Minimum t _{ON}	_	400	_	700	ns
t _{ON_MAX}	Maximum t _{ON}	_	_	35	_	μs
toff_MAX	Maximum t _{OFF}	-	_	200	-	μs
t _{OFF_MIN}	Minimum t _{OFF} (Note 6)	_	_	6	_	μs
Thermal Foldback and Ov	er-Temperature Protection Section					
T_{REG}	Overheating Temperature Regulation (Notes 6 & 8)	-	-	+140	_	°C
_	Shutdown Temperature (Notes 6 & 7 & 8)	_	_	+170	-	°C

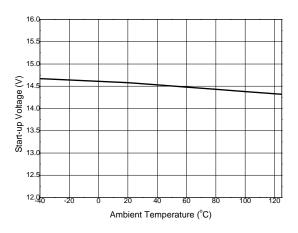
Notes:

^{6.} These parameters, although guaranteed by design, are not 100% tested in production.
7. The device will latch when OTP happen and the device won't operate constantly at this temperature.
8. This regulation temperature is junction temperature.

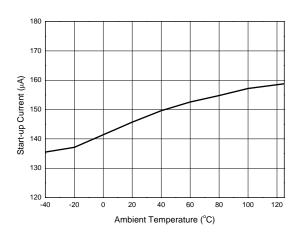


Performance Characteristics (Note 9)

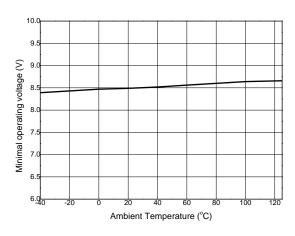
Start-up Voltage vs. Ambient Temperature



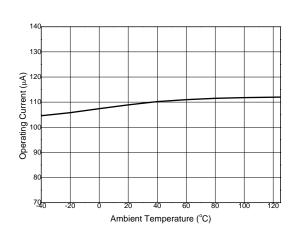
Start-up Current vs. Ambient Temperature



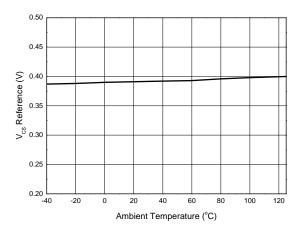
Minimal Operating Voltage vs. Ambient Temperature



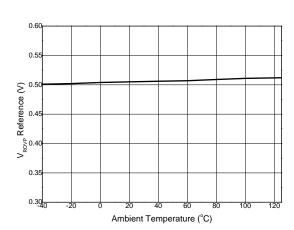
Operating Current vs. Ambient Temperature



V_{CS} Reference vs. Ambient Temperature



V_{ROVP} Reference vs. Ambient Temperature



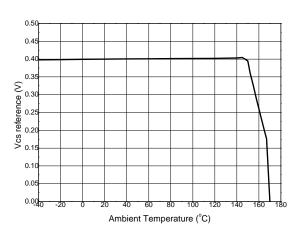


Performance Characteristics (continued) (Note 9)

VCC Clamp Voltage vs. Ambient Temperature

20 18 (2) 18 (2) 00 16 14 (3) 12 10 10 -40 -20 0 20 40 60 80 100 120 Ambient Temperature (°C)

Vcs Reference vs. Ambient Temperature



Note: 9. These electrical characteristics are tested under DC condition. The ambient temperature is equal to the junction temperature of the device.



Application Information

Convertor Operation

The AL1677 is designed for single-inductance buck application and is an extremely low BOM cost solution widely used in non-isolated situations. The AL1677 operates at boundary conduction mode (BCM) which can get good EMI performance. The device internally integrates a 500V high-voltage MOSFET. The AL1677 adopts a novel method to detect the t_{OFF} time and achieve an extremely low operation current, so the device does not need the auxiliary winding for V_{CC} supply and detecting the t_{OFF} time. It also has good constant current control which can guarantee the system current accuracy.

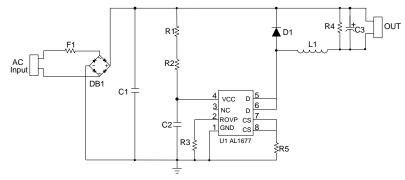


Figure 1 Typical Application Circuit

Start-up and Supply Voltage

Before start-up, the VCC capacitor C2 is charged by the startup resistors (R1, R2) from the high voltage mains. When the start-up voltage is reached, the AL1677 starts switching. During normal operation, the VCC supply is provided by start-up resisters (R1, R2) and internal source driver circuit.

The AL1677 has an internal VCC clamp voltage (typical 16.2V), which is limited by one internal active Zener diode.

When VCC voltage drops to below the undervoltage lockout (UVLO), switching is stop, the IC can restart when the voltage on VCC pin is exceeding the startup voltage $(V_{TH\ (ST)})$.

Protections

Undervoltage Lockout (UVLO)

When the voltage on the VCC pin drops to below $V_{OPR(Min)}$, the IC stops switching. The IC can restart when the voltage on VCC is exceeds the startup voltage ($V_{TH(ST)}$)

Leading-Edge Blanking (LEB)

To prevent false detection of the peak current of the inductor, a blanking time following switch-on is designed. When the internal switch turns on, a short current spike can occur because of the capacitive discharge of the voltage over the drain and source. It is disregarded during the LEB time (ton_min).

Cycle-by-cycle Overcurrent Protection (OCP)

The AL1677 has a built-in peak current detector. It triggers when the voltage on CS pin reaches the peak level V_{CS_CLAMP} . The R5 is connected to the CS pin to sense the current of the inductor. The maximum peak current ($I_{PEAK(MAX)}$) of the inductor can be calculated as below:

$$I_{PEAK} = \frac{V_{CS_REF}}{R5}$$

The detection circuit is activated after the LEB time. When the detection circuit sense the CS voltage is higher than 0.4V, the IC will turn off the switching to limit the output current. It automatically provides protection for the maximum LED current during operation. A propagation delay exists between overcurrent detection and actual source-switch off, so the actual peak current is a little higher than the OCP level set by the R5.

Output-Short Protection (OSP)

When LED is shorted, the device cannot detect the tope time, and the device controls the system operation at 5kHz low frequency.



Application Information (continued)

Output Open Protection (OVP)

AL1677 has output open-voltage protection controlled when the LED is open, which can prevent the output voltage from increasing to a very high value. This feature can help the system designer select a smaller volume capacitor. The output voltage is set by the external resistor R3, shown in Figure 1.

When LED is open, the toff time can be calculated as:

$$t_{off} = \frac{L1 \cdot V_{CS_REF}}{V_{OVP} \cdot R5}$$

Where

V_{OVP} is the output open voltage,

The output voltage is set by R3, and R3 is:

$$R3 = \frac{V_{ROVP_REF} \cdot t_{off}}{12 \cdot C_{REF} \cdot V_{CS_REF}} = \frac{V_{ROVP_REF} \cdot L1}{12 \cdot C_{REF} \cdot V_{OVP} \cdot R5}$$

Where

 V_{ROVP_REF} is the internal ROVP pin 0.5V's reference, C_{REF} is the internal 6pF capacitor.

Thermal Foldback Protection (TFP)

AL1677 has a thermal foldback function and adopts a self-adaptive control method, which can prevent the system from breaking down due to high temperatures. The overheating temperature is set at +140°C typical. When the junction temperature of the IC is higher than +140°C typical, the device will linearly decrease the internal reference voltage to decrease the output current. As a result of this feature, the device can control the system's output power at high ambient temperatures, to control the quantity of heat of the system. This enhances the safety of the system at high temperatures.

The thermal foldback waveform is shown below:

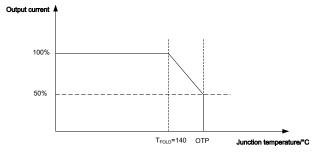


Figure 2. Thermal foldback waveform

Over-Temperature Protection (OTP)

The AL1677 has OTP protection function. When the junction temperature reach to +170°C typical, the IC will trigger an over-temperature protection condition which causes the device to shut down and latched. Once OTP has triggered, the system will resume after the system's AC source supply has been reset and power up.

Design Parameters

Setting the Current Sense Resistor R5

The AL1677 uses peak current control method to obtain constant current control and senses the peak current of the inductance cycle by cycle. The sample value is compared with the internal 0.4V reference. When the sampling value is up to 0.4V, the IC control of the internal MOSFET will turn off.

The peak current of the inductance is:



Application Information (continued)

$$I_{peak} = \frac{V_{CS_REF}}{R5}$$

Where,

 $V_{\text{CS_REF}}$ is the reference of the current sense, and the typical value is 0.4V. R5 is the current sense resistor.

In no PF buck topology, the system operates at boundary conduct mode. The output current is:

$$I_{o_mean} = \frac{1}{2} \cdot I_{peak}$$

Therefore, the current sense resistor R5 is determined:

$$R5 = \frac{1}{2} \cdot \frac{V_{CS_REF}}{I_{o_mean}}$$

Inductance Selection (L1)

The AL1677 controls the system operating at boundary conduction mode, and the systems' operating frequency does not keep constant because of the fluctuation of the bus voltage. Set the minimum switching frequency f_{min} at the maximum bus voltage, and the buck inductance value L1 can be calculated by:

$$L1 = \frac{(\sqrt{2}V_{in_rms} - V_o) \cdot R5 \cdot V_o}{V_{cs_ref} \cdot \sqrt{2}V_{in_rms} \cdot f_{min}}$$

Where,

Vo is the output voltage.

V_{in rms} is the RMS value of the input voltage.

According to the Faraday's Law of Induction, the winding number of the inductance can be calculated by:

$$N_{L1} = \frac{L1 \cdot I_{peak}}{A_a \cdot B_m} = \frac{L1 \cdot V_{CS_REF}}{A_a \cdot B_m \cdot R5}$$

Where

Ae is the core effective area.

B_m is the maximum magnetic flux density.

The AL1677 has designed the minimum t_{ON} time and maximum t_{ON} time. The t_{ON_MIN} is about 700ns and the t_{ON_MAX} time is about 35µs. In buck topology we can get the equation V_{in_rms} - V_{O} =L* I_{peak} / t_{ON} . If the inductance is very small, leading the t_{ON} to become smaller, when the system's t_{ON} is smaller than t_{ON_MIN} , the device cannot detect the peak current of the system, leading to incorrect output current. If the inductance is very large, leading t_{ON} to become larger when the system's t_{ON} is larger than the t_{ON_MAX} , the system's output current will decrease because of the limit of the t_{ON_MAX} . Therefore, the suitable value of the inductance is very important.

The AL1677 t_{OFF_MIN} time is about 6µS and t_{OFF_MAX} time is about 200µs. In buck topology we use the equation V_{O} =L* l_{peak} / t_{OFF} . If the inductance is very small, leading the t_{OFF} to become much smaller when the system's t_{OFF} is smaller than t_{OFF_MIN} , the system will enter DCM mode, and the output current will be incorrect. If the inductance is very large, leading t_{OFF} to become much larger when the system's t_{OFF} is larger than the t_{OFF_MAX} , the system will enter CCM mode, and the output current will also be incorrect. Therefore, the suitable value of the inductance is very important.

Consider these parameters, two examples of the typical application inductance is recommended as below:

System Spec.	Inductance Value	System Frequency	T _{ON} Min	T _{OFF}
60V/150mA (185~265V _{AC})	2.3mH	60K(230 V _{AC})	2.5μS(265 V _{AC})	11.5µS
42V/100mA (85~265 V _{AC})	2.5mH	62K(230 V _{AC})	1.7µs(265 V _{AC})	12.1µS



Application Information (continued)

Recommended Applications

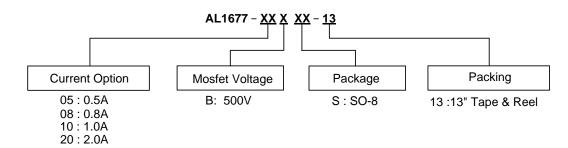
The AL1677 integrates different MOSFETs to adapt different wattage applications. The output current is limited by the internal integrated MOSFET, and the SO-8 package's heat dissipation capability. The minimum output voltage is limited by the LEB time, and is recommended to 15V. The recommended application is given below:

Device	Output Power Coverage	Maximum Output Current (Note 10)	Minimum Output Voltage
AL1677-05BS-13	≤5W	≤100mA	15V
AL1677-08BS-13	≤8W	≤120mA	15V
AL1677-10BS-13	≤10W	≤180mA	15V
AL1677-20BS-13	≤15W	≤240mA	15V

Note: 10. The higher output current is possible with extra power dissipation solution.



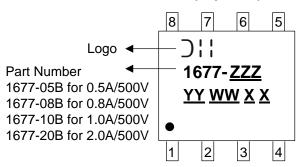
Ordering Information



Don't November	Bashana Oada	Danka wa	13" Tape and Reel		
Part Number	Package Code	Package	Quantity	Part Number Suffix	
AL1677-05BS-13	S	SO-8	4,000/Tape & Reel	-13	
AL1677-08BS-13	S	SO-8	4,000/Tape & Reel	-13	
AL1677-10BS-13	S	SO-8	4,000/Tape & Reel	-13	
AL1677-20BS-13	S	SO-8	4,000/Tape & Reel	-13	

Marking Information





<u>YY</u>: Year: 15,16,17 ~ <u>WW</u>: Week: 01~52; 52

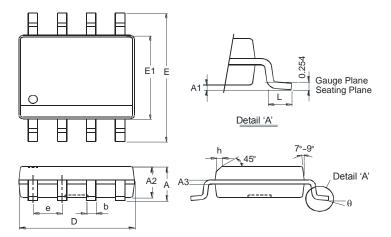
represents 52 and 53 week

XX: Internal Code



Package Outline Dimensions (All dimensions in mm (inch).)

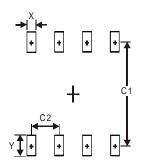
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SO-8				
Dim	Min	Max			
Α	-	1.75			
A 1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27	Тур			
h	-	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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